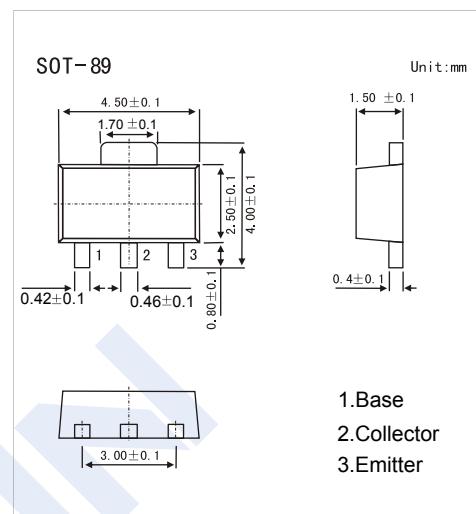


PNP Transistors

BCX51、BCX52、BCX53 (KCX51、KCX52、KCX53)

■ Features

- NPN Complements to BCX54,BCX55,BCX56
- Low Voltage
- High Current



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	VCBO	-45	V
		-60	V
		-100	V
Collector-emitter voltage	VCEO	-45	V
		-60	V
		-80	V
Emitter-base voltage	VEBO	-5	V
Collector current	Ic	-1	A
Peak collector current	ICM	-1.5	A
Peak base current	IBM	-200	mA
Total power dissipation	P _{tot}	1.3	W
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient	R _{th(j-a)}	94	K/W
Thermal resistance from junction to solder point	R _{th(j-s)}	14	K/W

BCX51、BCX52、BCX53 (KCX51、KCX52、KCX53)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -30\text{ V}, I_E = 0$			-100	nA
		$V_{CB} = -30\text{ V}, I_E = 0; T_j = 125^\circ\text{C}$			-10	uA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-100	nA
DC current gain	h_{FE}	$I_C = -5\text{ mA}; V_{CE} = -2\text{ V}$	63			
		$I_C = -150\text{ mA}; V_{CE} = -2\text{ V}$	63		250	
		$I_C = -500\text{ mA}; V_{CE} = -2\text{ V}$	40			
DC current gain BCX51-10,BCX52-10,BCX53-10 BCX51-16,BCX52-16,BCX53-16	h_{FE}	$I_C = -150\text{ mA}; V_{CE} = -2\text{ V}$	63		160	
		$I_C = -150\text{ mA}; V_{CE} = -2\text{ V}$	100		250	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$			-500	mV
Base to emitter voltage	V_{BE}	$I_C = -500\text{ mA}; V_{CE} = -2\text{ V}$			-1	V
Transition frequency	f_T	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$		50		MHz

■ hFE Classification

TYPE	BCX51	BCX51-10	BCX51-16
Marking	AA	AC	AD
TYPE	BCX52	BCX52-10	BCX52-16
Marking	AE	AG	AM
TYPE	BCX53	BCX53-10	BCX53-16
Marking	AH	AK	AL

■ Typical Characteristics

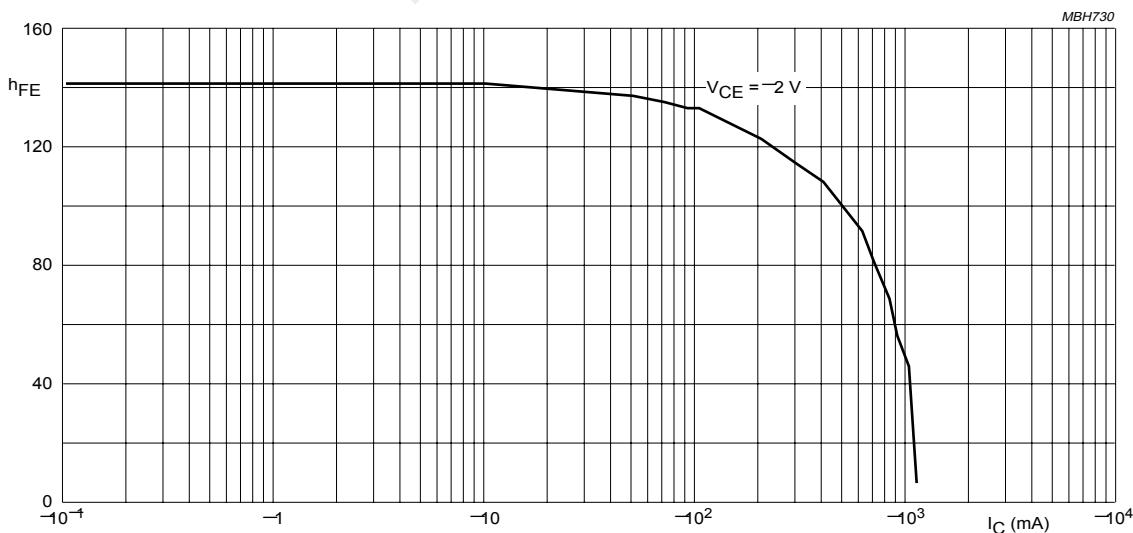


Fig.1 DC current gain; typical values.